

Specification Sheet

Silicon Wafer P Type

(4 inch, Boron Doped)

Stock No: NS6130-10-1201, CAS: 7440-21-3

Product	:	Silicon Wafer
Stock No	:	NS6130-10-1201
CAS	:	7440-21-3
Diameter	:	4" (100mm)
Thickness	:	525 ± 25 μm
Crystal Orientation	:	< 100>
Type	:	P Type
Growth Method	:	FZ
Resistivity	:	1.0-5.0Ω.cm
TTV	:	< 10.0μm
STIR	:	< 2μm
GLOBAL TIR	:	< 5μm
Warp	:	< 50.0μm
LPD	:	< 30 counts @ particles size>0.3μm
Laser Mark	:	None
Surface	:	Single Side Polished
Doping	:	Boron
Bow	:	< 50.0μm
Main Inspect Verifier	:	Manager QC

Note: Product Specification are subject to amendment and may change over time

Characterization of Silicon Wafer P Type



Silicon Wafer P Type



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